



N-Channel 20-V (D-S) MOSFET

PRODUCT SUMMARY

V_{DS} (V)	$R_{DS(on)}$ (Ω)	I_D (A) ^a	Q_g (Typ.)
20	0.046 at $V_{GS} = 4.5$ V	6	3.5 nC
	0.063 at $V_{GS} = 2.5$ V	6	

FEATURES

- Halogen-free According to IEC 61249-2-21
- TrenchFET[®] Power MOSFET
- New Thermally Enhanced PowerPAK[®] SC-75 Package
 - Small Footprint Area
 - Low On-Resistance
- Typical ESD Protection 560 V

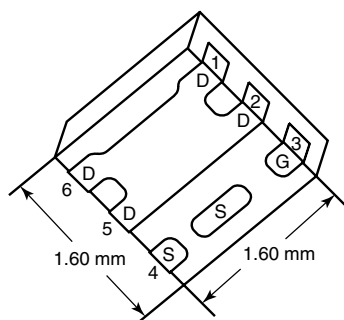


RoHS
COMPLIANT
HALOGEN
FREE

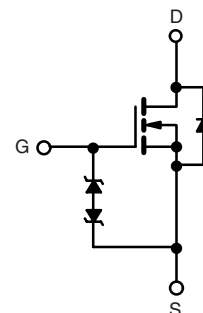
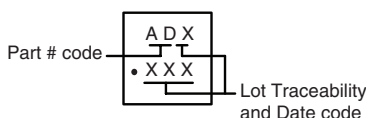
APPLICATIONS

- Load Switch for Portable Applications
- High Frequency DC/DC Converter

PowerPAK SC-75-6L-Single



Marking Code



Ordering Information: SiB406EDK-T1-GE3 (Lead (Pb)-free and Halogen-free)

N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS $T_A = 25$ °C, unless otherwise noted

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	20	V
Gate-Source Voltage	V_{GS}	± 12	
Continuous Drain Current ($T_J = 150$ °C)	$T_C = 25$ °C	6 ^a	A
	$T_C = 70$ °C	6 ^a	
	$T_A = 25$ °C	5.1 ^{b, c}	
	$T_A = 70$ °C	4.1 ^{b, c}	
Pulsed Drain Current	I_{DM}	15	A
Continuous Source-Drain Diode Current	$T_C = 25$ °C	6 ^a	
	$T_A = 25$ °C	1.6 ^{b, c}	
Maximum Power Dissipation	$T_C = 25$ °C	10	W
	$T_C = 70$ °C	6.4	
	$T_A = 25$ °C	1.95 ^{b, c}	
	$T_A = 70$ °C	1.25 ^{b, c}	
Operating Junction and Storage Temperature Range	T_J, T_{stg}	- 55 to 150	°C
Soldering Recommendations (Peak Temperature) ^{d, e}		260	

THERMAL RESISTANCE RATINGS

Parameter	Symbol	Typical	Maximum	Unit
Maximum Junction-to-Ambient ^{b, f}	R_{thJA}	51	64	°C/W
Maximum Junction-to-Case (Drain)	R_{thJC}	10	12.5	

Notes:

a. Package limited

b. Surface Mounted on 1" x 1" FR4 board.

c. $t = 5$ s.d. See Solder Profile (www.vishay.com/ppg?73257). The PowerPAK SC-75 is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection.

e. Rework Conditions: manual soldering with a soldering iron is not recommended for leadless components.

f. Maximum under Steady State conditions is 100 °C/W.

SPECIFICATIONS T _J = 25 °C, unless otherwise noted						
Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
Static						
Drain-Source Breakdown Voltage	V _{DS}	V _{GS} = 0 V, I _D = 250 μA	20			V
V _{DS} Temperature Coefficient	ΔV _{DS} /T _J	I _D = 250 μA		23		mV/°C
V _{GS(th)} Temperature Coefficient	ΔV _{GS(th)} /T _J			- 3.3		
Gate-Source Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = 250 μA	0.6		1.4	V
Gate-Source Leakage	I _{GSS}	V _{DS} = 0 V, V _{GS} = ± 12 V			± 8	μA
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = 20 V, V _{GS} = 0 V			- 1	
		V _{DS} = 20 V, V _{GS} = 0 V, T _J = 55 °C			- 10	
On-State Drain Current ^a	I _{D(on)}	V _{DS} ≥ 5 V, V _{GS} = 4.5 V	10			A
Drain-Source On-State Resistance ^a	R _{DS(on)}	V _{GS} = 4.5 V, I _D = 3.9 A		0.037	0.046	Ω
		V _{GS} = 2.5 V, I _D = 3.3 A		0.051	0.063	
Forward Transconductance ^a	g _{fs}	V _{DS} = 10 V, I _D = 3.9 A		14		S
Dynamic ^b						
Input Capacitance	C _{iss}	V _{DS} = 10 V, V _{GS} = 0 V, f = 1 MHz		350		pF
Output Capacitance	C _{oss}			63		
Reverse Transfer Capacitance	C _{rss}			37		
Total Gate Charge	Q _g	V _{DS} = 10 V, V _{GS} = 10 V, I _D = 5.1 A		7.5	12	nC
		V _{DS} = 10 V, V _{GS} = 4.5 V, I _D = 5.1 A		3.5	5.5	
Gate-Source Charge	Q _{gs}			0.95		
Gate-Drain Charge	Q _{gd}			0.75		
Gate Resistance	R _g	f = 1 MHz		3.5		Ω
Turn-On Delay Time	t _{d(on)}	V _{DD} = 10 V, R _L = 2.4 Ω I _D ≅ 4.1 A, V _{GEN} = 4.5 V, R _g = 1 Ω		10	15	ns
Rise Time	t _r			12	20	
Turn-Off Delay Time	t _{d(off)}			18	30	
Fall Time	t _f			12	20	
Turn-On Delay Time	t _{d(on)}	V _{DD} = 10 V, R _L = 2.4 Ω I _D ≅ 4.1 A, V _{GEN} = 10 V, R _g = 1 Ω		5	10	
Rise Time	t _r			12	20	
Turn-Off Delay Time	t _{d(off)}			15	25	
Fall Time	t _f			10	15	
Drain-Source Body Diode Characteristics						
Continuous Source-Drain Diode Current	I _S	T _C = 25 °C			6	A
Pulse Diode Forward Current	I _{SM}				15	
Body Diode Voltage	V _{SD}	I _S = 4.1 A, V _{GS} = 0 V		0.8	1.2	V
Body Diode Reverse Recovery Time	t _{rr}	I _F = 4.1 A, dI/dt = 100 A/μs, T _J = 25 °C		15	30	ns
Body Diode Reverse Recovery Charge	Q _{rr}			8	20	nC
Reverse Recovery Fall Time	t _a			8		ns
Reverse Recovery Rise Time	t _b			7		

Notes:

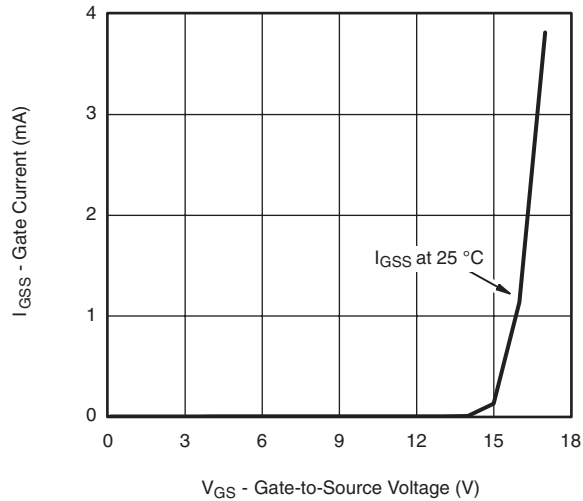
a. Pulse test; pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$

b. Guaranteed by design, not subject to production testing.

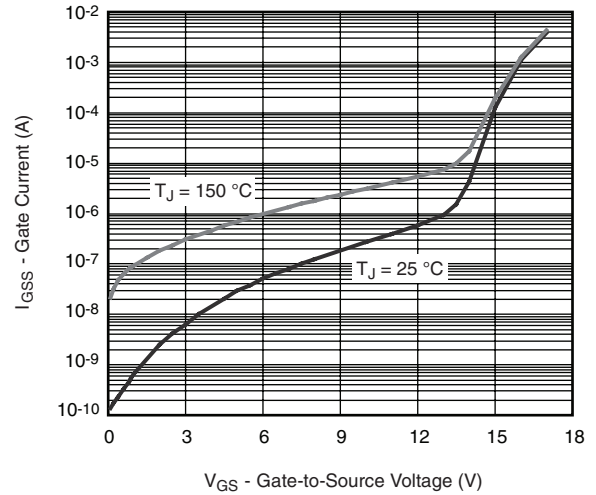
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



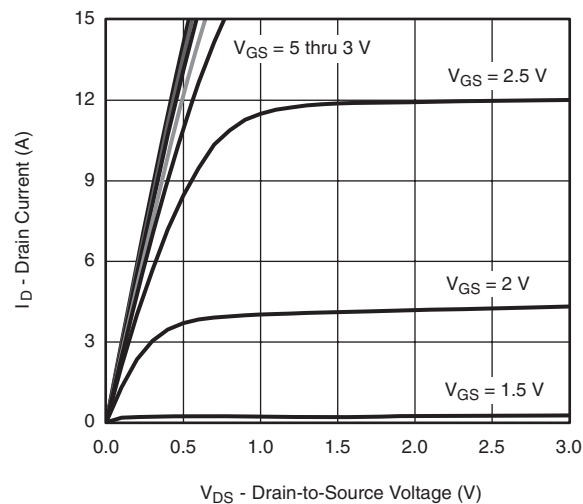
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



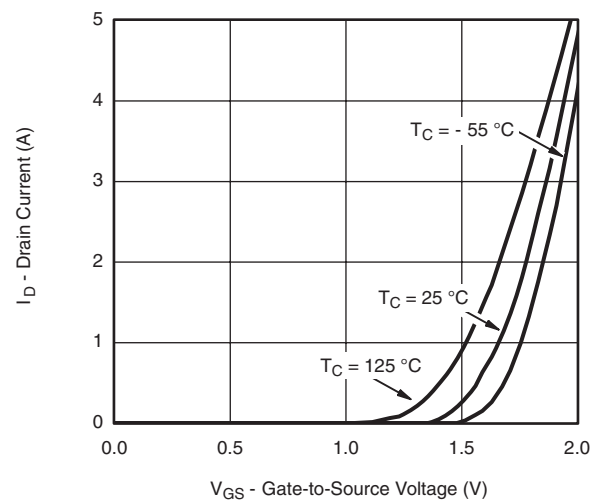
Gate Current vs. Gate-Source Voltage



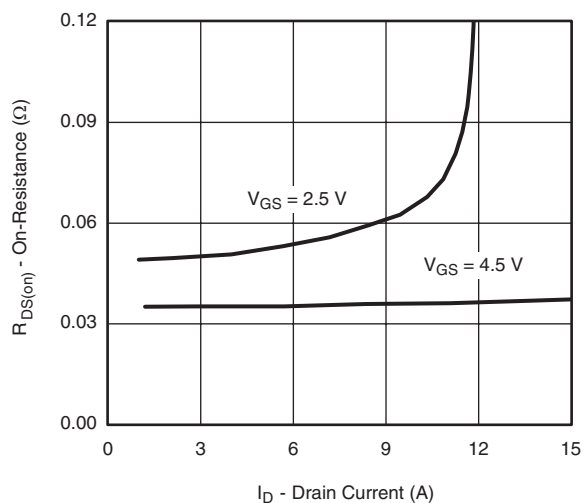
Gate Current vs. Gate-Source Voltage



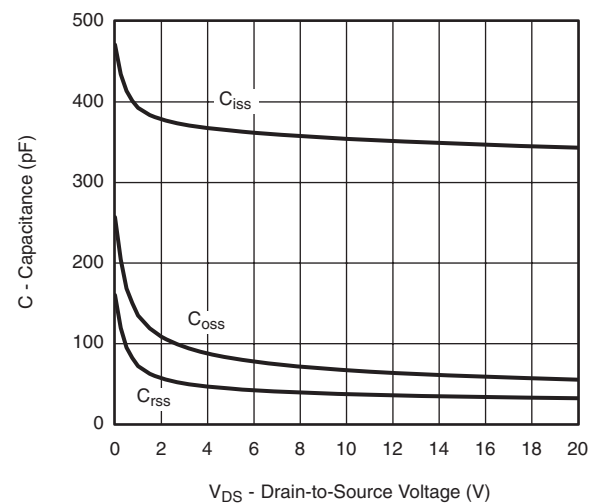
Output Characteristics



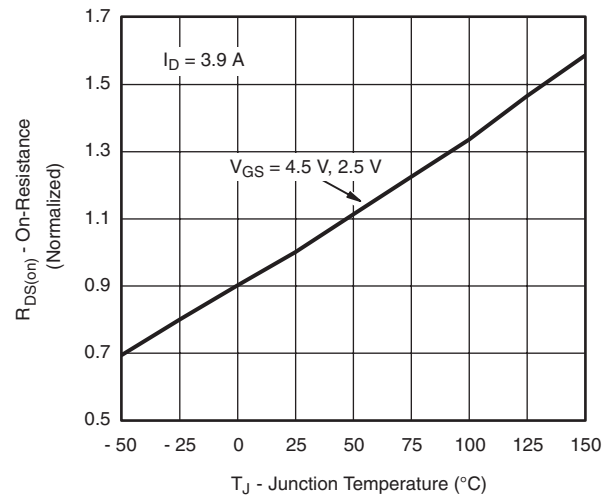
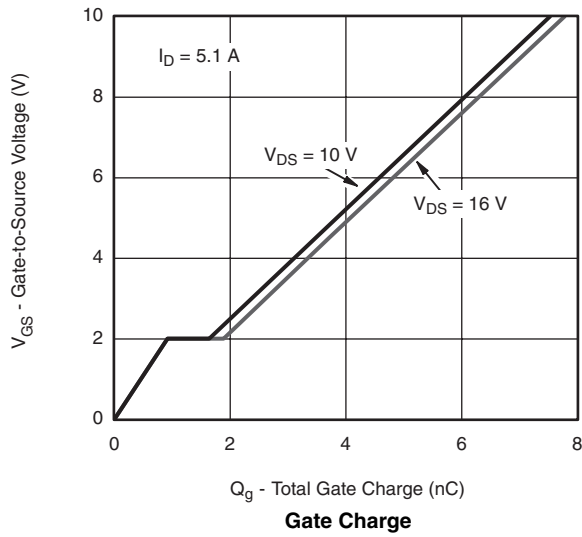
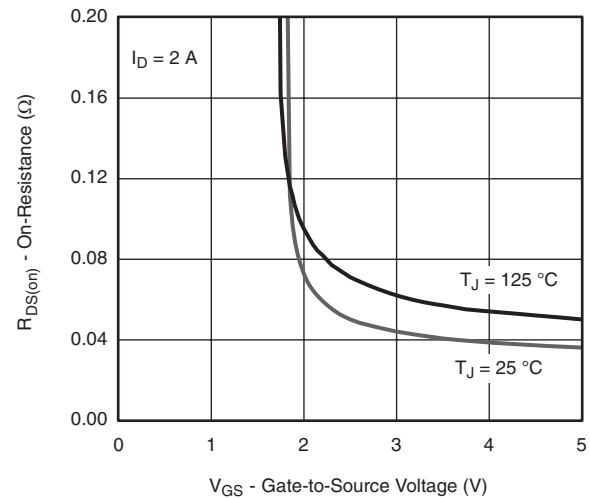
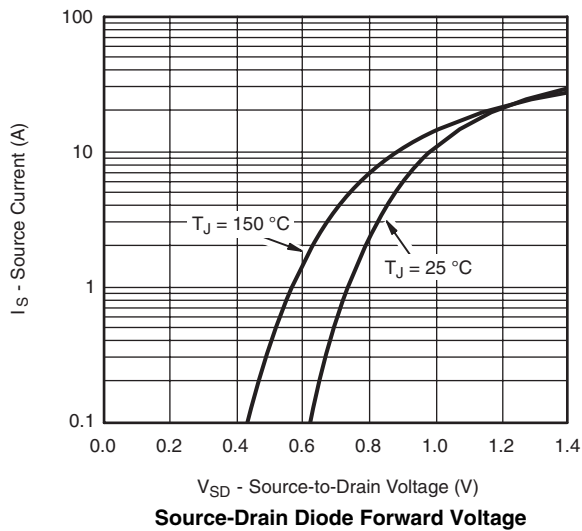
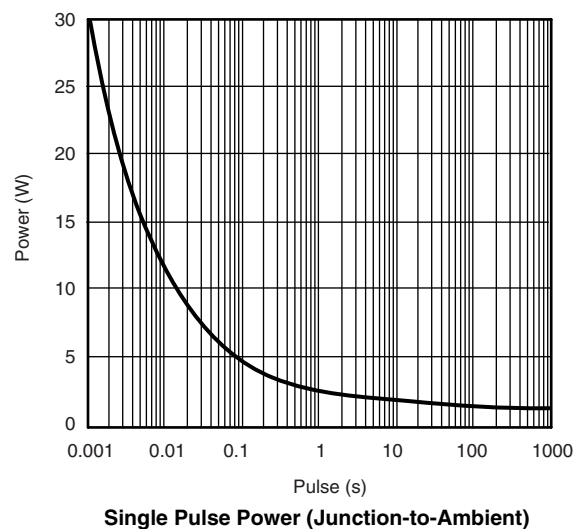
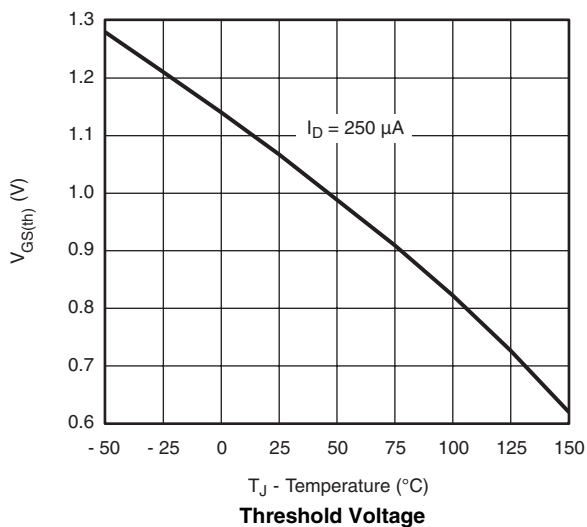
Transfer Characteristics



On-Resistance vs. Drain Current and Gate Voltage

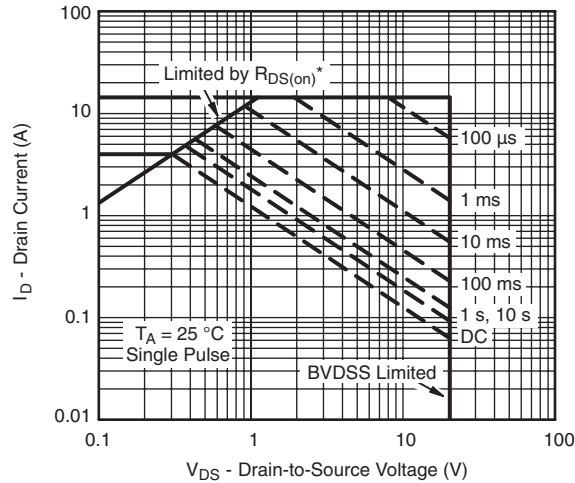


Capacitance

TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted**On-Resistance vs. Junction Temperature****On-Resistance vs. Gate-to-Source Voltage**

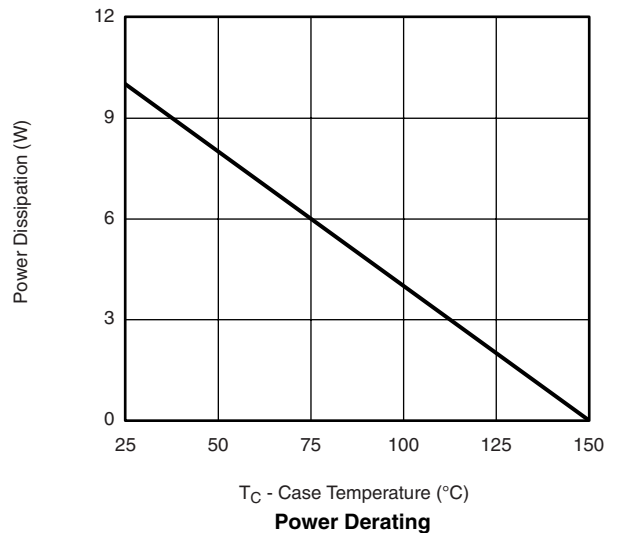
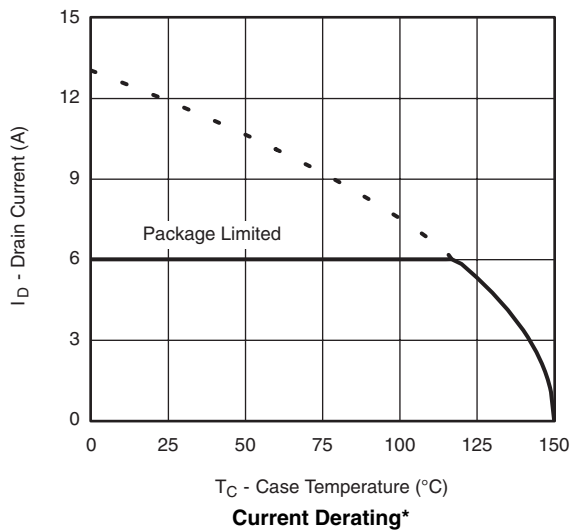


TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

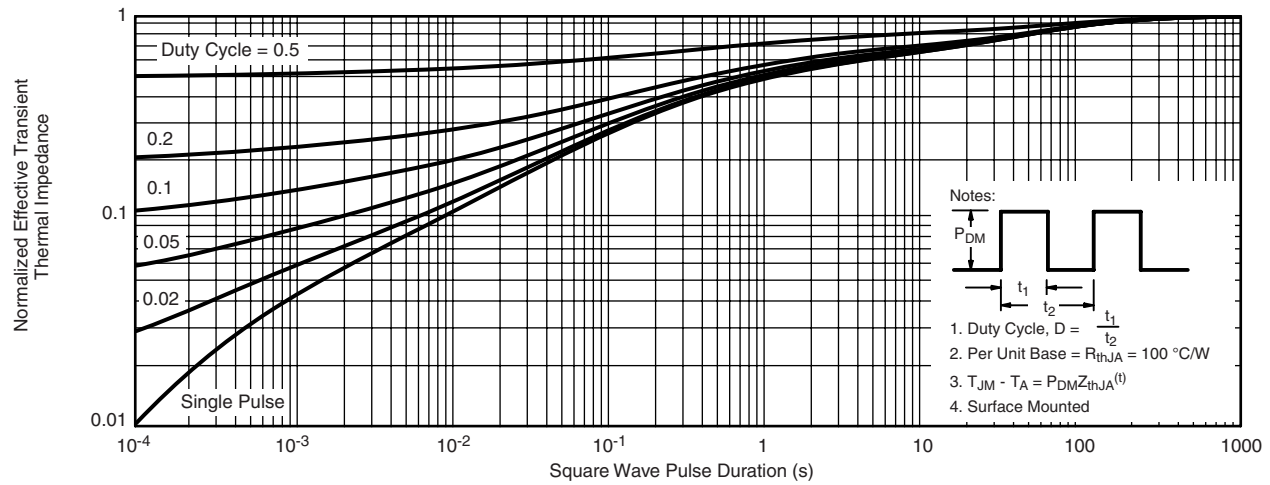
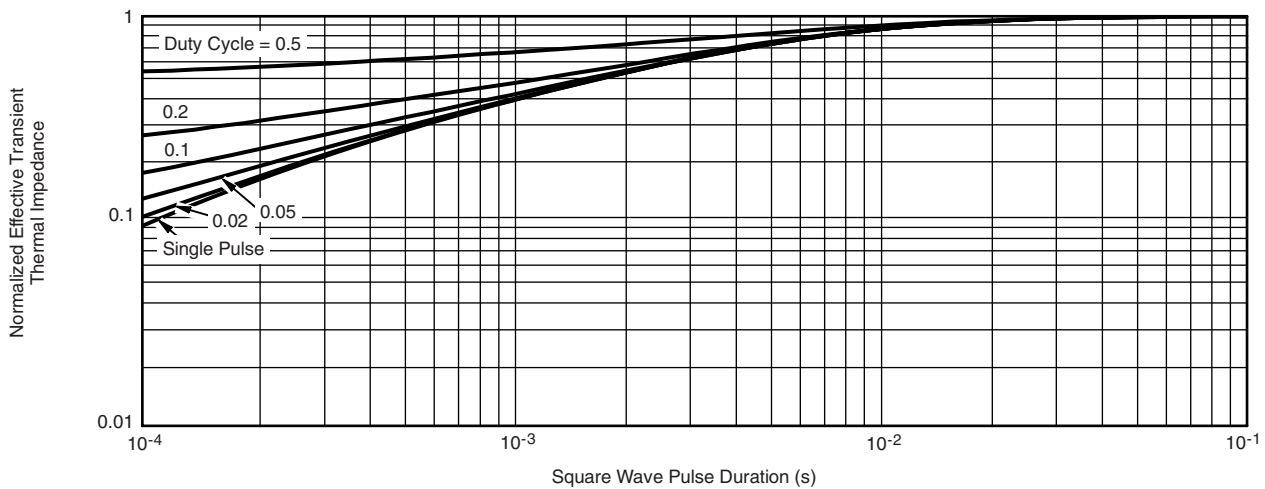


* $V_{GS} >$ minimum V_{GS} at which $R_{DS(on)}$ is specified

Safe Operating Area, Junction-to-Ambient



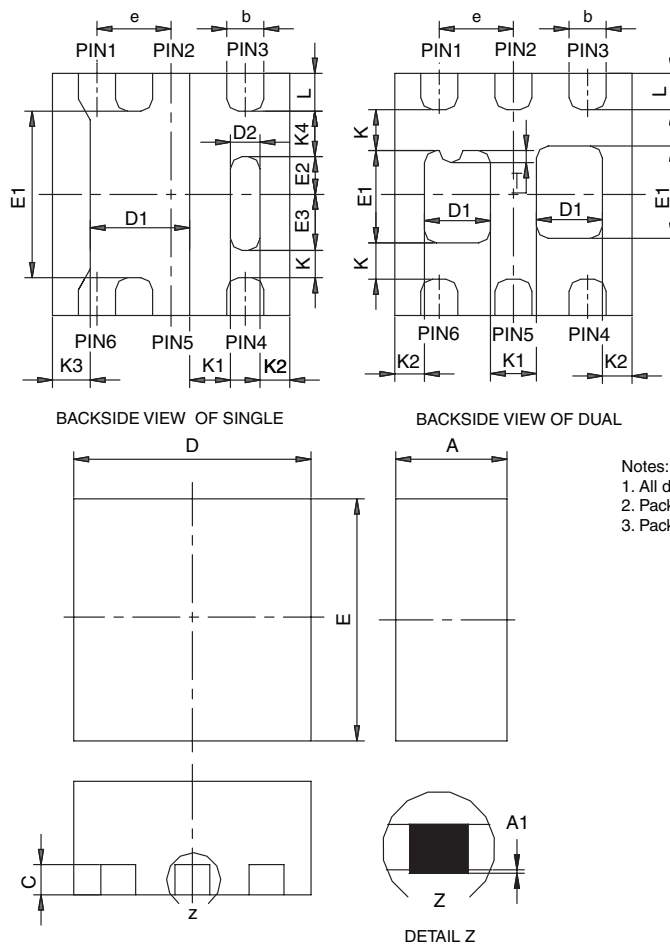
* The power dissipation P_D is based on $T_{J(max)} = 150$ °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.

TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted**Normalized Thermal Transient Impedance, Junction-to-Ambient****Normalized Thermal Transient Impedance, Junction-to-Case**

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PowerPAK® SC75-6L



- Notes:
1. All dimensions are in millimeters
 2. Package outline exclusive of mold flash and metal burr
 3. Package outline inclusive of plating

DIM	SINGLE PAD						DUAL PAD					
	MILLIMETERS			INCHES			MILLIMETERS			INCHES		
	Min	Nom	Max	Min	Nom	Max	Min	Nom	Max	Min	Nom	Max
A	0.675	0.75	0.80	0.027	0.030	0.032	0.675	0.75	0.80	0.027	0.030	0.032
A1	0	-	0.05	0	-	0.002	0	-	0.05	0	-	0.002
b	0.18	0.25	0.33	0.007	0.010	0.013	0.18	0.25	0.33	0.007	0.010	0.013
C	0.15	0.20	0.25	0.006	0.008	0.010	0.15	0.20	0.25	0.006	0.008	0.010
D	1.53	1.60	1.70	0.060	0.063	0.067	1.53	1.60	1.70	0.060	0.063	0.067
D1	0.57	0.67	0.77	0.022	0.026	0.030	0.34	0.44	0.54	0.013	0.017	0.021
D2	0.10	0.20	0.30	0.004	0.008	0.012						
E	1.53	1.60	1.70	0.060	0.063	0.067	1.53	1.60	1.70	0.060	0.063	0.067
E1	1.00	1.10	1.20	0.039	0.043	0.047	0.51	0.61	0.71	0.020	0.024	0.028
E2	0.20	0.25	0.30	0.008	0.010	0.012						
E3	0.32	0.37	0.42	0.013	0.015	0.017						
e	0.50 BSC			0.020 BSC			0.50 BSC			0.020 BSC		
K	0.180 TYP			0.007 TYP			0.245 TYP			0.010 TYP		
K1	0.275 TYP			0.011 TYP			0.320 TYP			0.013 TYP		
K2	0.200 TYP			0.008 TYP			0.200 BSC			0.008 TYP		
K3	0.255 TYP			0.010 TYP								
K4	0.300 TYP			0.012 TYP								
L	0.15	0.25	0.35	0.006	0.010	0.014	0.15	0.25	0.35	0.006	0.010	0.014
T							0.03	0.08	0.13	0.001	0.003	0.005

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DWG: 5935

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Офис по работе с юридическими лицами:

105318, г.Москва, ул.Щербаковская д.3, офис 1107, 1118, ДЦ «Щербаковский»

Телефон: +7 495 668-12-70 (многоканальный)

Факс: +7 495 668-12-70 (доб.304)

E-mail: info@moschip.ru

Skype отдела продаж:

moschip.ru

moschip.ru_4

moschip.ru_6

moschip.ru_9